HGN170A10AL P-1

100V N-Ch Power MOSFET

Feature

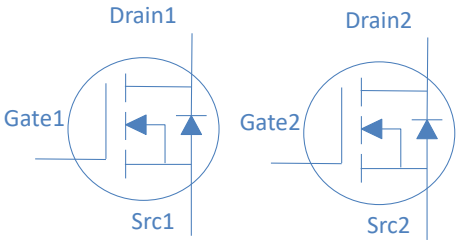
◇ High Speed Power Switching, Logic Level
◇ Enhanced Body diode dv/dt capability
◇ Enhanced Avalanche Ruggedness
◇ 100% UIS Tested, 100% Rg Tested
◇ Lead Free, Halogen Free

V_{DS}		100	V
$R_{DS(on),typ}$	V_{GS}=10V	14	mΩ
$R_{DS(on),typ}$	V_{GS}=4.5V	22	mΩ
$I_{D\ (Sillicon\ Limited)}$		34.8	A
$I_{D\ (Package\ Limited)}$		28	A

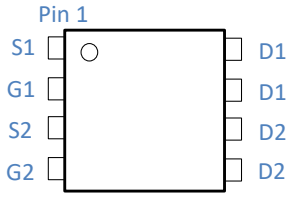
Application

◇ Synchronous Rectification in SMPS
◇ Hard Switching and High Speed Circuit
◇ DC/DC in Telecoms and Inductrial

DFN5*6



Part Number	Package	Marking
HGN170A10AL	DFN5*6	GN170A10AL



Absolute Maximum Ratings at T_j=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C=25℃	35	A
		T_C=100℃	25	
Continuous Drain Current (Package Limited)		T_C=25℃	28	
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	180	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C=25℃	45	mJ
Power Dissipation	P_D	T_C=25℃	31	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to150	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	55	℃/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	4	℃/W

Electrical Characteristics at T_j=25℃ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	1.4	2.0	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=100V, T_j=25℃	-	-	1	μA
		V_{GS}=0V, V_{DS}=100V, T_j=100℃	-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=15A	-	14	17	mΩ
		V_{GS}=4.5V, I_D=10A	-	22	26	
Transconductance	g_{fs}	V_{DS}=5V, I_D=15A	-	42	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz	-	1.6	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=50V, f=1MHz	-	840	-	pF
Output Capacitance	C_{oss}		-	147	-	
Reverse Transfer Capacitance	C_{rss}		-	4.9	-	
Total Gate Charge	Q_g(10V)	V_{DD}=50V, I_D=15A, V_{GS}=10V	-	16	-	nC
Total Gate Charge	Q_g(4.5V)		-	9	-	
Gate to Source Charge	Q_{gs}		-	3	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	3	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=50V, I_D=15A, V_{GS}=10V, R_G=10Ω,	-	6	-	ns
Rise time	t_r		-	3	-	
Turn off Delay Time	$t_{d(off)}$		-	13	-	
Fall Time	t_f		-	3	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=50V, I_F=15A, dI_F/dt=500A/μs	-	30	-	ns
Reverse Recovery Charge	Q_{rr}		-	105	-	nC

Fig 1. Typical Output Characteristics

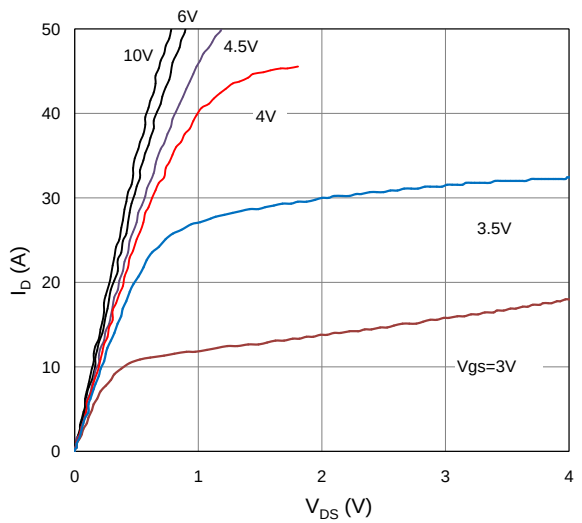


Figure 2. On-Resistance vs. Gate-Source Voltage

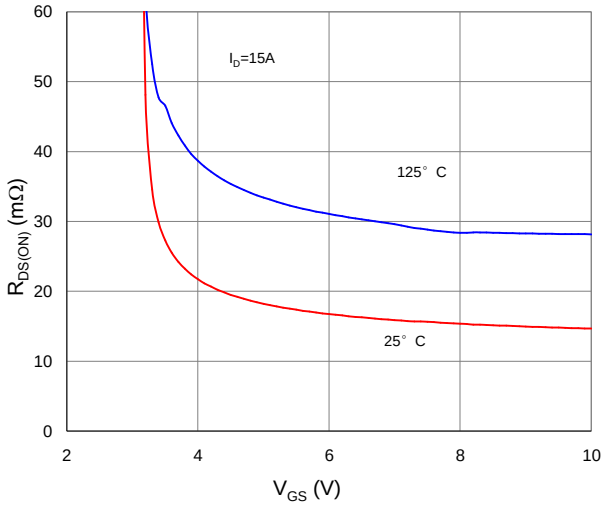


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

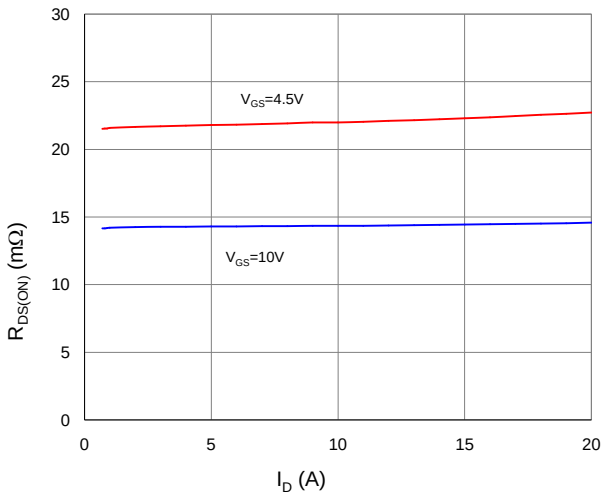


Figure 4. Normalized On-Resistance vs. Junction Temperature

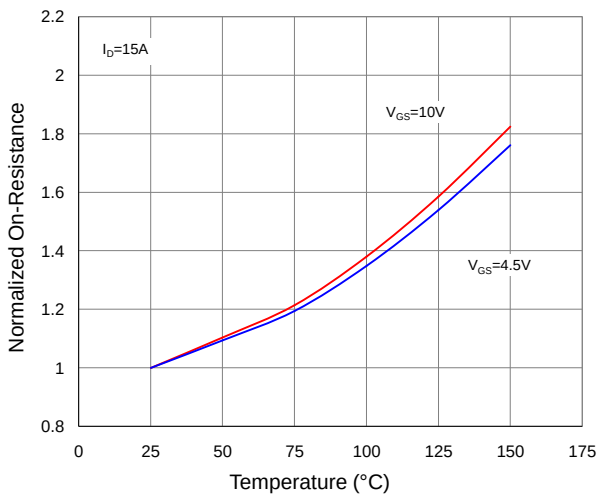


Figure 5. Typical Transfer Characteristics

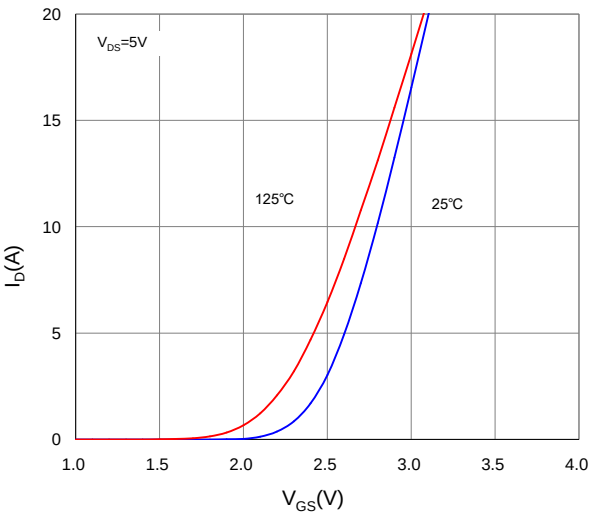


Figure 6. Typical Source-Drain Diode Forward Voltage

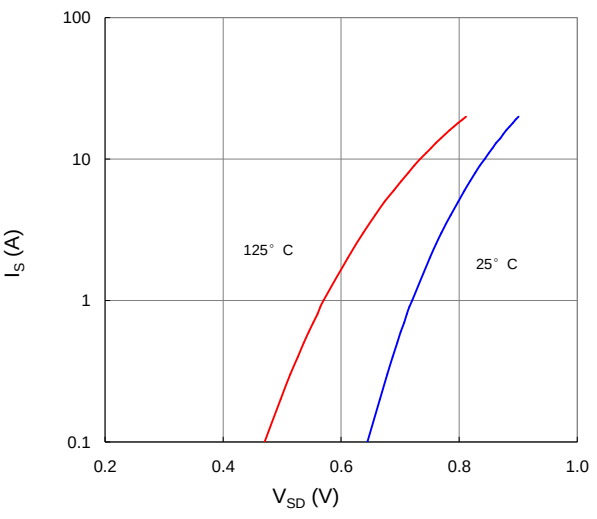


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

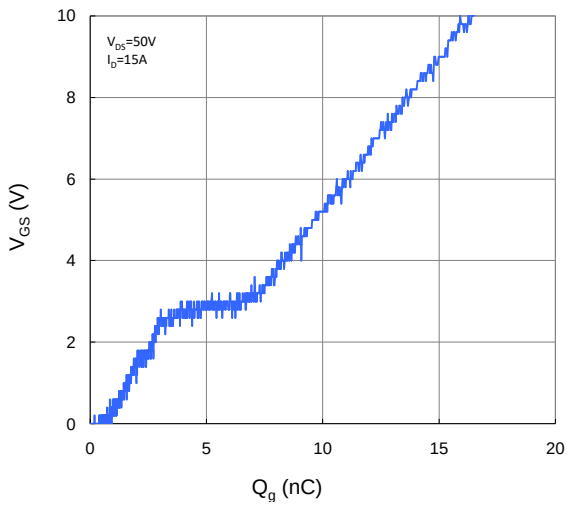


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

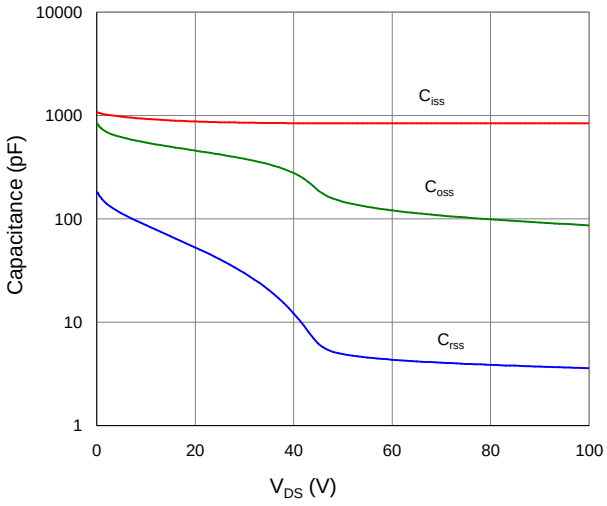


Figure 9. Maximum Safe Operating Area

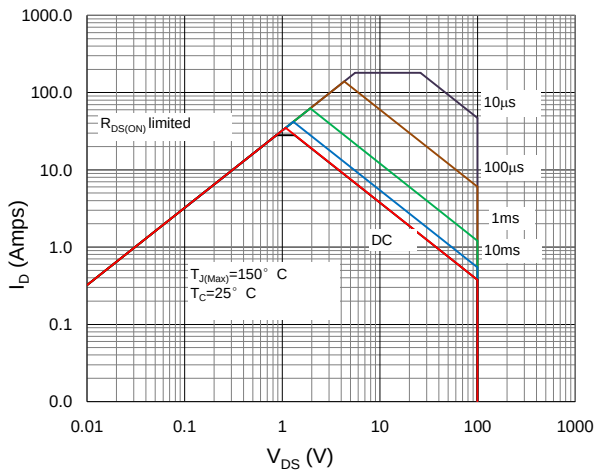


Figure 10. Maximun Drain Current vs. Case Temperature

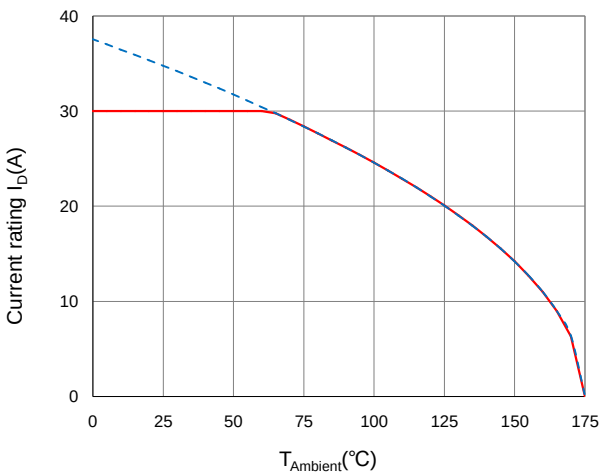
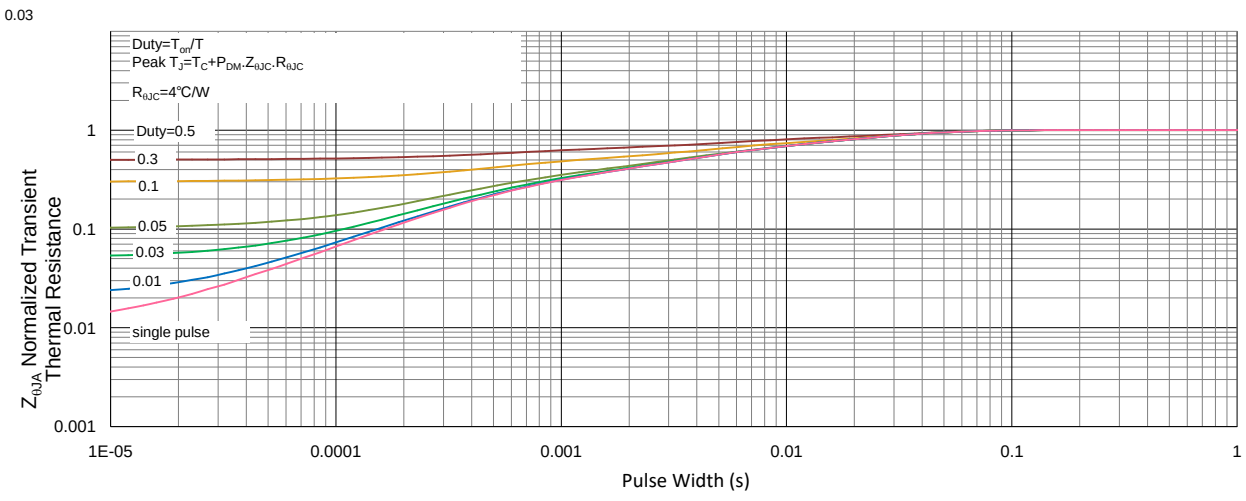
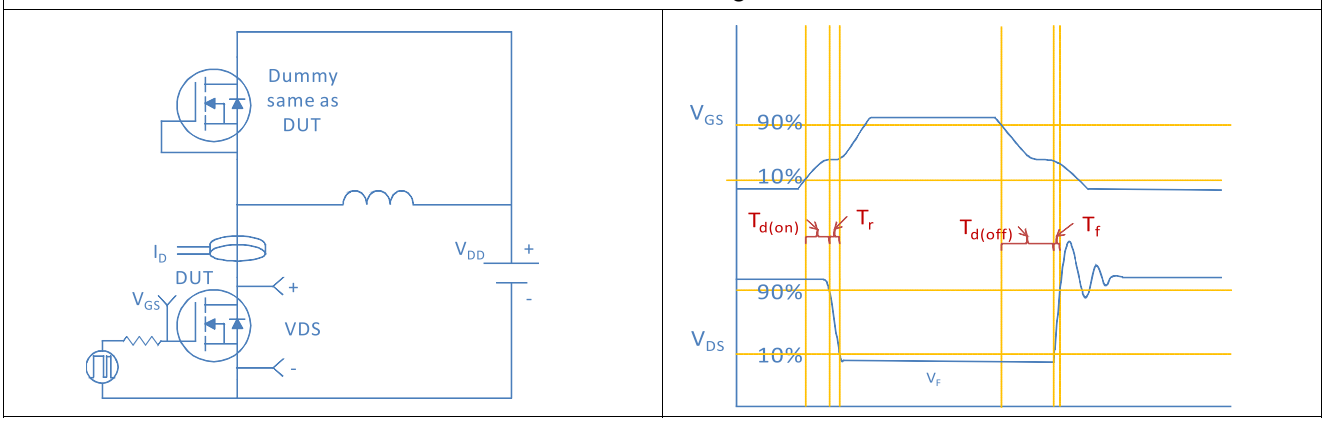


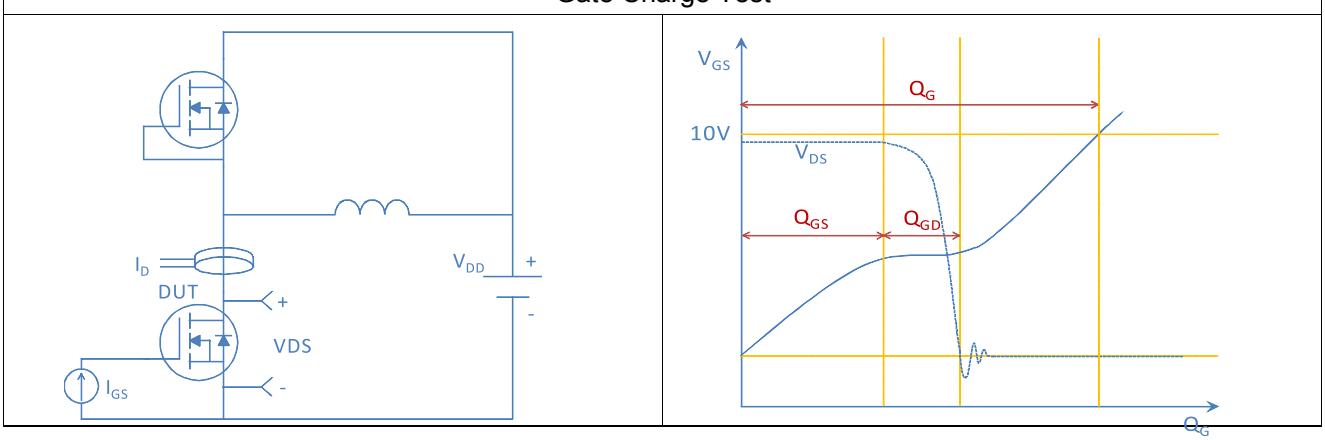
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



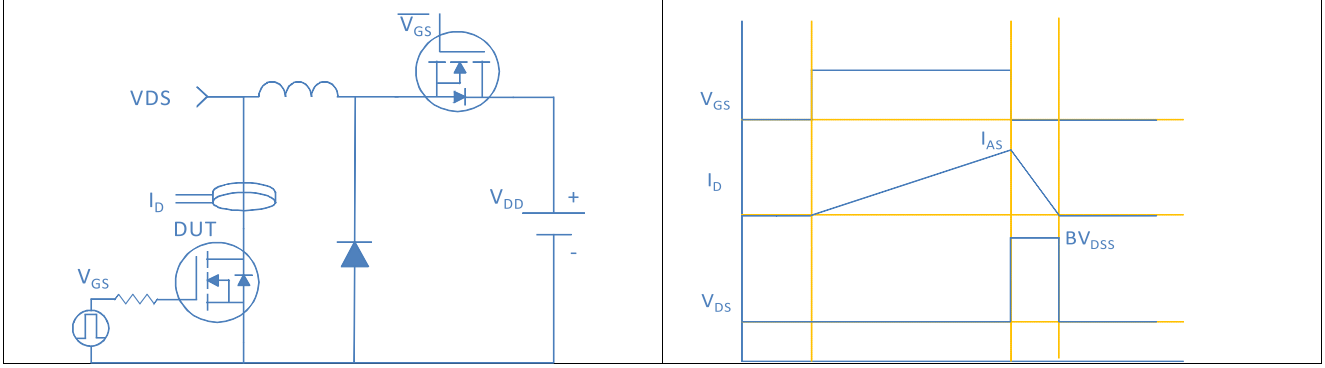
Inductive switching Test



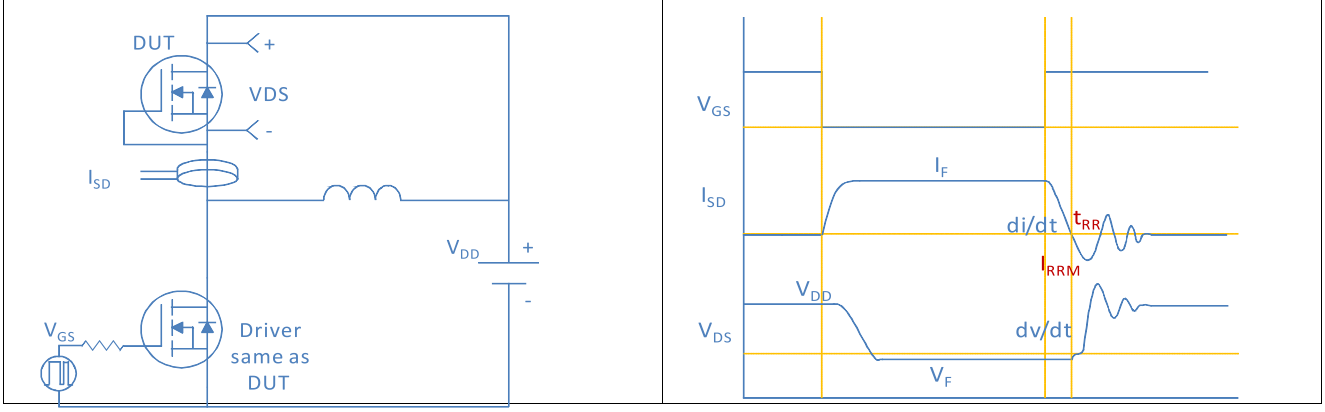
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

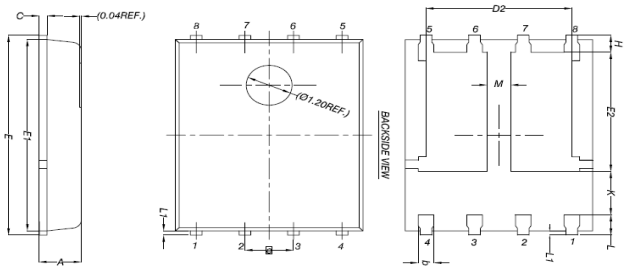


Diode Recovery Test



Package Outline

DFN5x6_P, 8 Leads



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	-	-
α	0°	-	12°

Land Pattern
(Only for Reference)